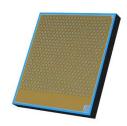
# V00155

Die; 2222; 940; M; 3B; G10X36; 3W-2J; 0.9X1.0



### **Features:**

Chip Technology: GaAs VCSEL

Laser Wavelength: 940

Optical Power Class: 7.4 W pulsed

— Radiation Profile: Multi-Mode

ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)

# **Ordering Information**

Description Operating Mode: Ordering Code

 $T_a = 25$ °C;  $I_F = 4$  A;  $t_p = 100 \ \mu s$ ; DC = 1%

Die; 2222; 940; M; 3B; 7.4 W V00155

G10X36; 3W-2J; 0.9X1.0





COMPLIES WITH IEC 60825-1,  $3^{\rm rd}$  EDITION MAY 2014. COMPLIES WITH 21 CFR 1040.10 AND 1040-10.11 EXCEPT FOR DEVIATIONS PURSUANT TO LASER NOTICE NO.50 DATED 27 MAY 2001.



# **Maximum Ratings**

 $T_a = 25$ °C

Parameter	Symbol		Values
Operation/Solder temperature	Ts	min.	-20°C
$t_p = 100 \ \mu s; DC = 1\%$		max.	100°C
Storage temperature	T <sub>stg</sub>	min.	-20°C
		max.	110°C
Forward current	<b>I</b> f	max.	8.5 A
Pulsed operation; $T_p$ = 100 $\mu$ s; DC = 1%; $T_S$ = 25°C			
Forward current	<b>I</b> f	max.	3.5 A
Direct current operation; DC = 100%; Ts = 25°C			
Reverse Voltage	Not designed for reverse operation		
ESD withstand voltage	VESD	max.	2 kV
acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)			

Note: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device.



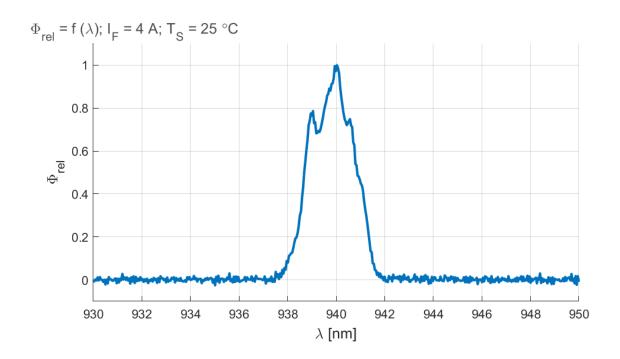
# **Characteristics**

 $T_a = 25$ °C,  $I_F = 4$  A;  $t_p = 100~\mu s$ ; DC = 1%

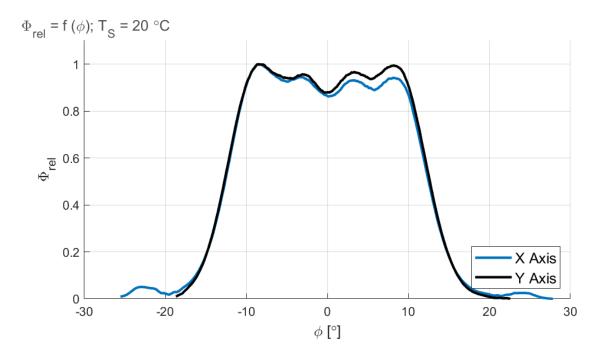
Parameter	Symbol		Values
Forward voltage	VF	typ.	3.9 V
Output power	Φ	typ.	7.4 W
Threshold current	I <sub>th</sub>	typ.	0.5 A
Slope efficiency	SE	typ.	2.0 W / A
Power conversion efficiency	η	typ.	50%
Peak wavelength	λpeak	min.	930 nm
		typ.	940 nm
		max.	950 nm
Spectral bandwidth at FWHM (50% of $\Phi_{\text{max}}$ )	λεwhm	typ.	2 nm
Temperature coefficient of wavelength	$TC_\lambda$	typ.	0.07 nm / K
Field of view at FWHC (50% of $\Phi_{max}$ )	<b>φ</b> χ	typ.	25°
	<b>⁄</b> Y	typ.	25°



# Relative Spectral Emission 1)

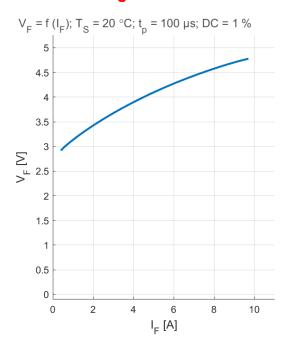


# Radiation Characteristics 1)

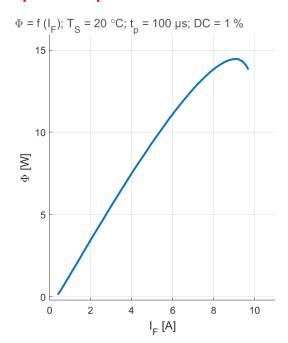




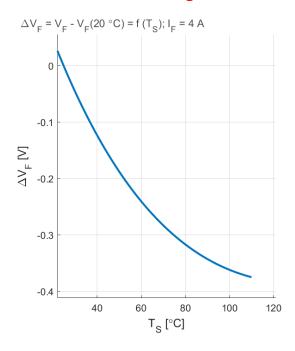
# Forward Voltage 1) 2)



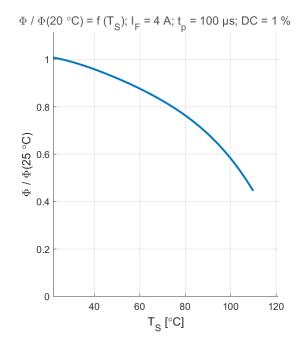
# Optical Output Power 1) 2)



### Relative Forward Voltage 1)



### Relative Radiant Power 1)

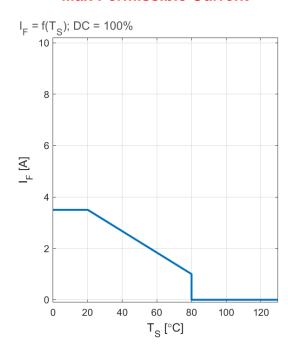




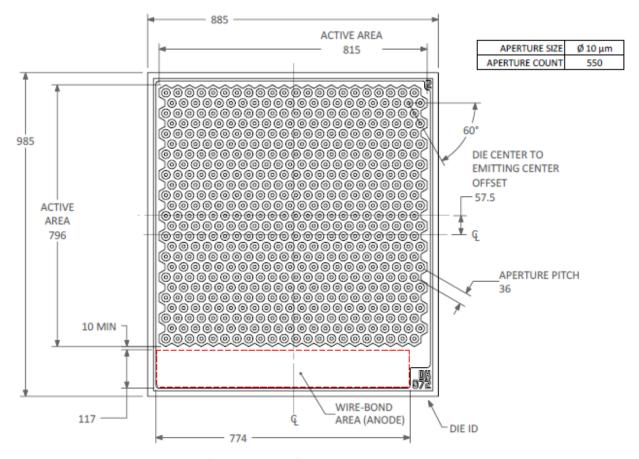
### **Max Permissible Pulse Current**

# I<sub>F</sub> = f(T<sub>S</sub>); t<sub>p</sub> = 100 μs; DC = 1 % 8 6 2 0 20 40 60 80 100 120 T<sub>S</sub> [°C]

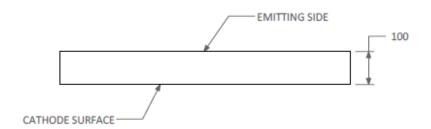
### **Max Permissible Current**



### Dimension Drawings 3)



DASHED LINES (WIRE-BOND AREA) ARE NOT VISIBLE ON ACTUAL DIE





# **Product Label**

VIXAR Vertical Cavity Surface Emitting Laser (VCSEL) Product				
Model:				
Manufacturer: VIXAR 2355 Polaris AVE N. SUITE 100 Plymouth, MN 55447 USA				
Manufactured: Bare Die by VIXAR, Fabricated or Packaged by: City:, Country:				
Wafer #:  Date Code:  Manufacturer Lot No.:  Quantity:				
Complies with FDA/CDRH 21 CFR 1040.10 and 1040.11 except for deviations pursuant to Laser Notice No. 50, dated June 24, 2007.				
CDRH Accession No.: 1210159-000 Product Code: RDW				



### **Notes**

Depending on the mode of operation, these devices emit highly concentrated visible and non-visible light which can be hazardous to the human eye. Products which incorporate these devices must follow the safety precautions given in IEC 60825-1.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related information please visit <a href="www.vixarinc.com/applications/application-notes">www.vixarinc.com/applications/application-notes</a>



### **Glossary**

- Typical Values: Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- Testing temperature:  $T_a = 25^{\circ}C$
- Tolerance of Measure: Unless otherwise noted in drawing, tolerances are specified with ±0.1 and dimensions are specified in mm.



# **Revision History**

Version	Date	Change
0.0	September 15th - 2020	Initiation of preliminary datasheet
1.0	March 1 <sup>st</sup> – 2021	Release of datasheet





COMPLIES WITH IEC 60825-1,  $3^{\rm st}$  EDITION MAY 2014. COMPLIES WITH 21 CFR 1040.10 AND 1040-10.11 EXCEPT FOR DEVIATIONS PURSUANT TO LASER NOTICE NO.50 DATED 27 MAY 2001.

